

High Voltage Transistor Surface Mount

NPN Silicon

PZTA42T1G

Features

- PZTA42T1G is Complement to PZTA92T1G
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Rating	Value	Unit
V_{CEO}	Collector-Emitter Voltage (Open Base)	300	Vdc
V_{CBO}	Collector-Base Voltage (Open Emitter)	300	Vdc
V_{EBO}	Emitter-Base Voltage (Open Collector)	6.0	Vdc
I_C	Collector Current (DC)	500	mAdc
P_D	Total Power Dissipation @ $T_A = 25^\circ\text{C}$ (Note 1)	1.5	W
T_{stg}	Storage Temperature Range	-65 to +150	$^\circ\text{C}$
T_J	Junction Temperature	150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

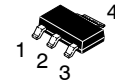
- Device mounted on a FR-4 glass epoxy printed circuit board
1.575 in x 1.575 in x 0.0625 in; mounting pad for the collector lead = 0.93 sq in.

THERMAL CHARACTERISTICS

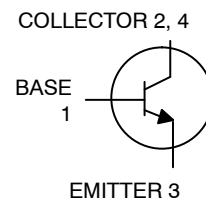
Symbol	Characteristic	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	83.3	$^\circ\text{C/W}$

- Device mounted on a FR-4 glass epoxy printed circuit board
1.575 in x 1.575 in x 0.0625 in; mounting pad for the collector lead = 0.93 sq in.

SOT-223 PACKAGE NPN SILICON HIGH VOLTAGE TRANSISTOR SURFACE MOUNT



SOT-223
CASE 318E
STYLE 1



PZTA42T1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Characteristics	Min	Max	Unit
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage (Note 3) ($I_C = 1.0\text{ mAdc}$, $I_B = 0$)	300	–	Vdc
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_C = 100\text{ }\mu\text{Adc}$, $I_E = 0$)	300	–	Vdc
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_E = 100\text{ }\mu\text{Adc}$, $I_C = 0$)	6.0	–	Vdc
I_{CBO}	Collector-Base Cutoff Current ($V_{CB} = 200\text{ Vdc}$, $I_E = 0$)	–	0.1	μAdc
I_{EBO}	Emitter-Base Cutoff Current ($V_{BE} = 6.0\text{ Vdc}$, $I_C = 0$)	–	0.1	μAdc

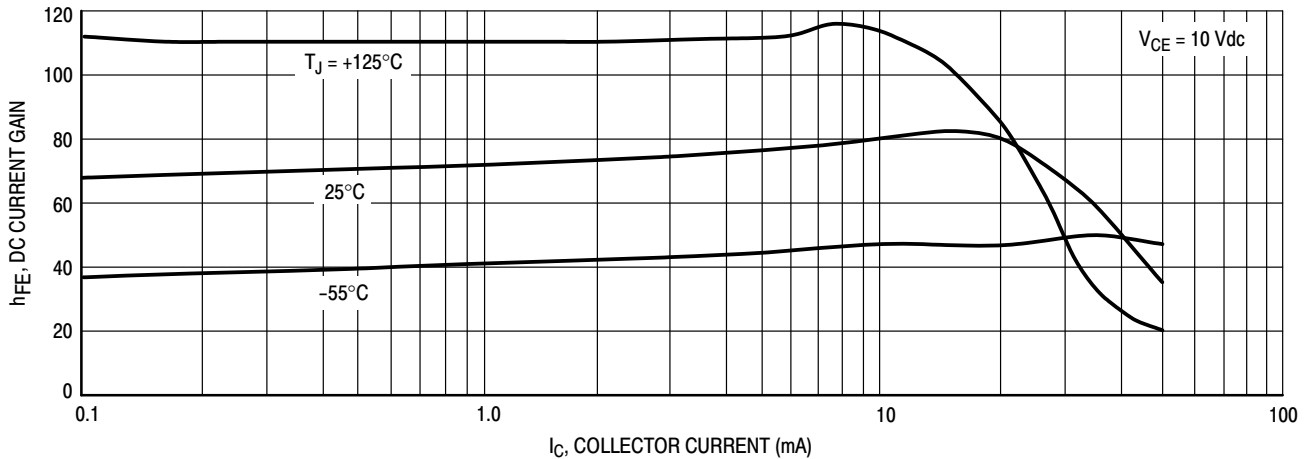
ON CHARACTERISTICS

h_{FE}	DC Current Gain ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 30\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$)	25 40 40	– – –	–
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DYNAMIC CHARACTERISTICS

f_T	Current-Gain – Bandwidth Product ($I_C = 10\text{ mAdc}$, $V_{CE} = 20\text{ Vdc}$, $f = 100\text{ MHz}$)	50	–	MHz
C_{re}	Feedback Capacitance ($V_{CB} = 20\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	–	3.0	pF
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($I_C = 20\text{ mAdc}$, $I_B = 2.0\text{ mAdc}$)	–	0.5	Vdc
$V_{BE(sat)}$	Base-Emitter Saturation Voltage ($I_C = 20\text{ mAdc}$, $I_B = 2.0\text{ mAdc}$)	–	0.9	Vdc

3. Pulse Test Conditions, $t_p = 300\text{ }\mu\text{s}$, $\delta = 0.02$.



PZTA42T1G

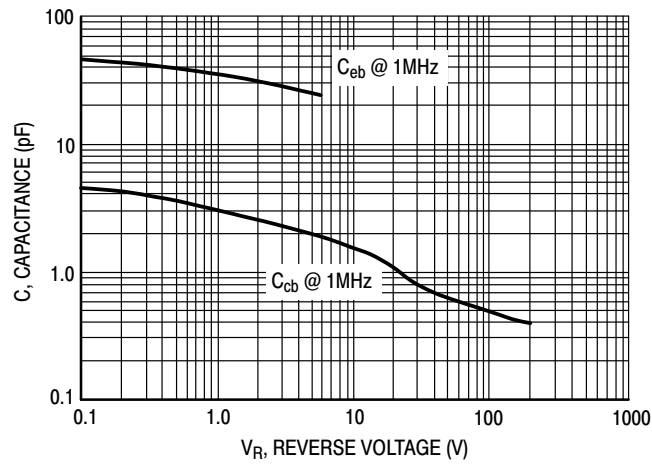


Figure 2. Capacitance

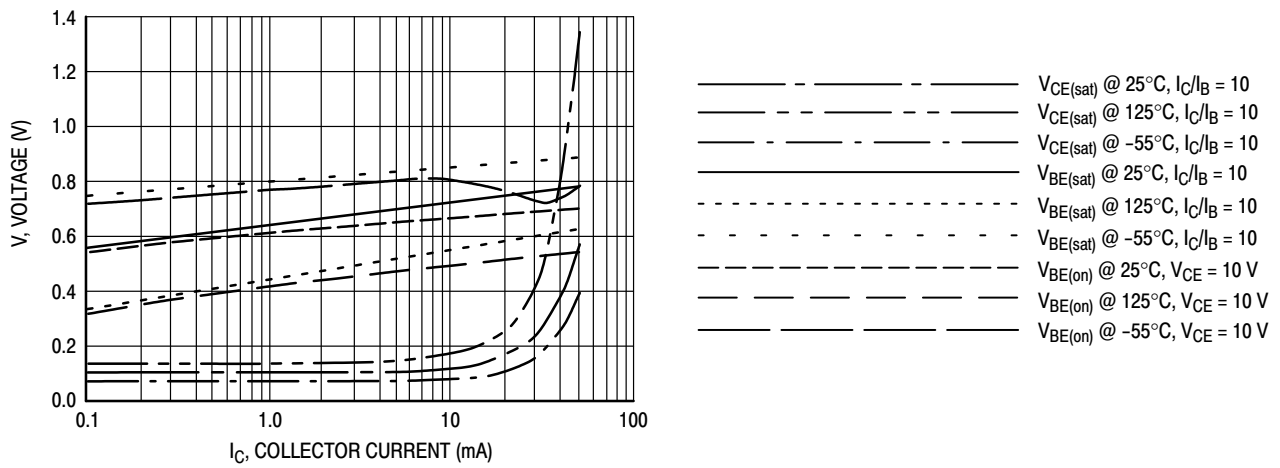


Figure 3. "ON" Voltages

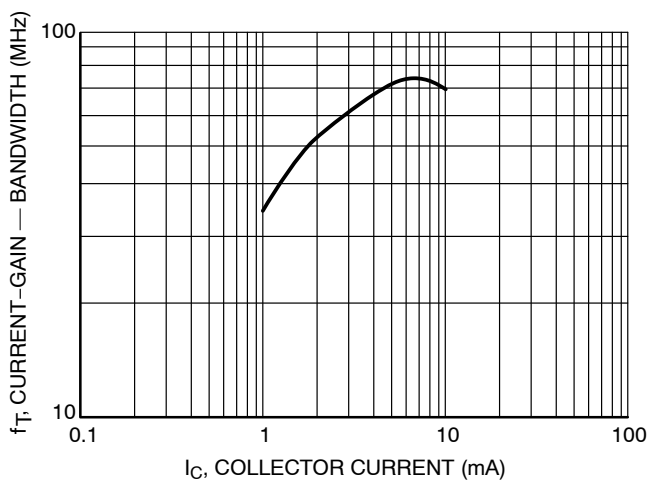


Figure 4. Current Gain Bandwidth Product

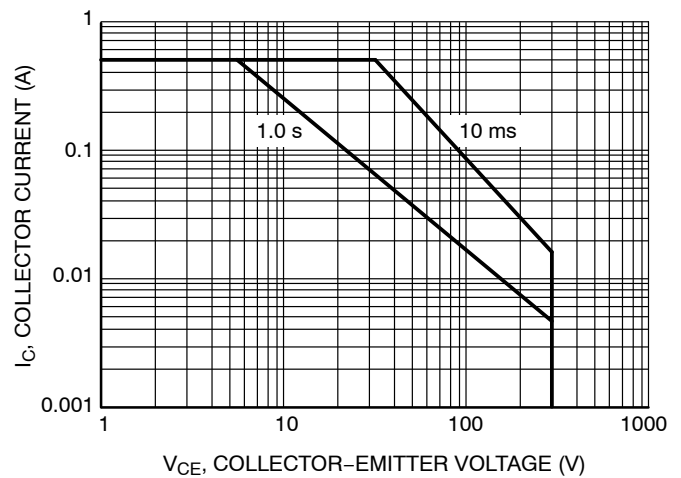


Figure 5. Safe Operating Area



SCALE 1:1

SOT-223 (TO-261)
CASE 318E-04
ISSUE R

DATE 02 OCT 2018



TOP VIEW



SIDE VIEW



FRONT VIEW



DETAIL A

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
4. DATUMS A AND B ARE DETERMINED AT DATUM H.
5. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

MILLIMETERS			
DIM	MIN.	NOM.	MAX.
A	1.50	1.63	1.75
A1	0.02	0.06	0.10
b	0.60	0.75	0.89
b1	2.90	3.06	3.20
c	0.24	0.29	0.35
D	6.30	6.50	6.70
E	3.30	3.50	3.70
e</			

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